Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

IGBT (NPT) Module

V_{CES} = 2x 1200 V
I_{C25} = 135 A
$V_{CE(sat)}$ = 2.2 V

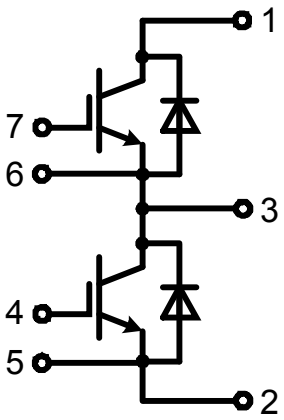
Phase leg

Part number

MII100-12A3

Backside: isolated

E72873



Features / Advantages:

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

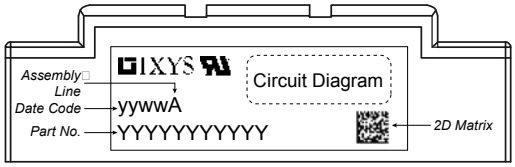
Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1200	V
V_{GES}	*max. DC gate voltage*					±20	V
V_{GEM}	*max. transient gate emitter voltage*					±30	V
I_{C25}	*collector current*		T_C = 25°C			135	A
I_{C80}			T_C = 80°C			90	A
P_{tot}	*total power dissipation*		T_C = 25°C			560	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 75A; V_{GE} = 15 V	T_{VJ} = 25°C		2.2	2.7	V
			T_{VJ} = 125°C		2.7		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 3mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	4.5	5.5	6.5	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C			5	mA
			T_{VJ} = 125°C		7.5		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				300	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 75 A			350		nC
$t_{d(on)}$	*turn-on delay time*				100		ns
t_r	*current rise time*				50		ns
$t_{d(off)}$	*turn-off delay time*	inductive load	T_{VJ} = 125°C		650		ns
t_f	*current fall time*	V_{CE} = 600 V; I_C = 75 A			50		ns
E_{on}	*turn-on energy per pulse*	V_{GE} = ±15 V; R_G = 15 Ω			12.1		mJ
E_{off}	*turn-off energy per pulse*				10.5		mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 15 Ω	T_{VJ} = 125°C				
I_{CM}		V_{CEmax} = 1200 V				150	A
SCSOA	*short circuit safe operating area*	V_{CEmax} = 1200 V					
t_{SC}	*short circuit duration*	V_{CE} = 1200 V; V_{GE} = ±15 V	T_{VJ} = 125°C			10	µs
I_{SC}	*short circuit current*	R_G = 15 Ω; non-repetitive			270		A
R_{thJC}	*thermal resistance junction to case*					0.22	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.22		K/W

Diode							
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			1200	V
I_{F25}	*forward current*		T_C = 25°C			150	A
I_{F80}			T_C = 80°C			95	A
V_F	*forward voltage*	I_F = 75A	T_{VJ} = 25°C			2.50	V
			T_{VJ} = 125°C		1.70		V
I_R	*reverse current*	V_R = V_{RRM}	T_{VJ} = 25°C			1	mA
			T_{VJ} = 125°C		1.5		mA
Q_{rr}	*reverse recovery charge*	V_R = 600 V			7		µC
I_{RM}	*max. reverse recovery current*	-di_F/dt = 600 A/µs	T_{VJ} = 125°C		62		A
t_{rr}	*reverse recovery time*	I_F = 75A; V_{GE} = 0 V			200		ns
E_{rec}	*reverse recovery energy*				1.2		mJ
R_{thJC}	*thermal resistance junction to case*					0.45	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.45		K/W

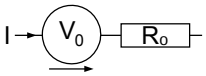
Package Y4					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					300	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		125	°C
Weight						110		g
M_D	*mounting torque*				2.25		2.75	Nm
M_T	*terminal torque*				4.5		5.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	14.0	10.0			mm
$d_{Spb/Apb}$			*terminal to backside*	16.0	16.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3600			V
		t = 1 minute			3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MII100-12A3	MII100-12A3	Box	6	466743

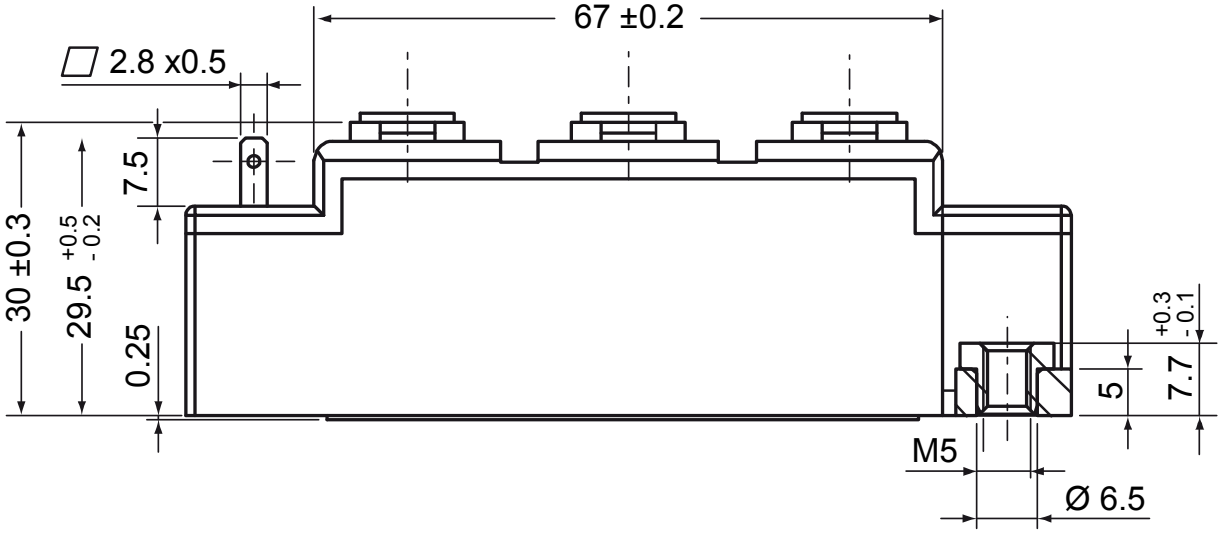
Equivalent Circuits for Simulation

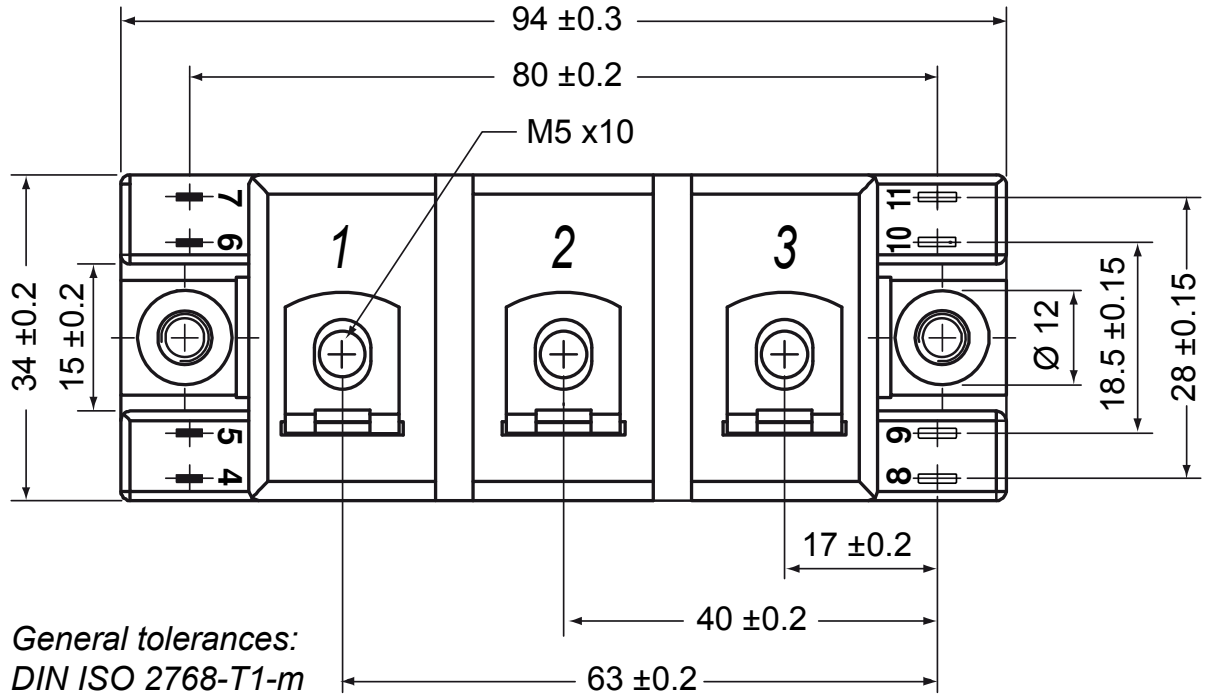
** on die level* T_{VJ} = 150 °C

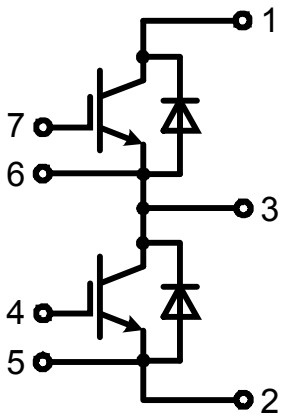


		IGBT	Diode	
$V_{0\,max}$	*threshold voltage*	1.5	1.3	V
$R_{0\,max}$	*slope resistance **	13.6	6.5	mΩ

Outlines Y4







IGBT

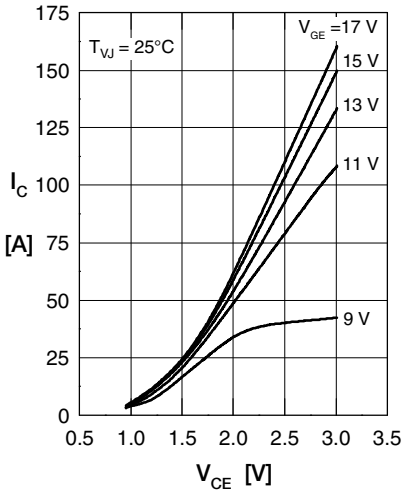


Fig. 1 Typ. output characteristics

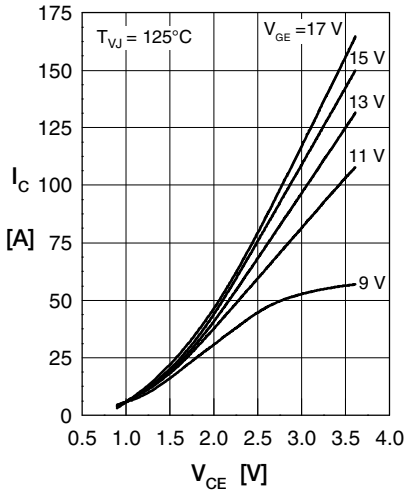


Fig. 2 Typ. output characteristics

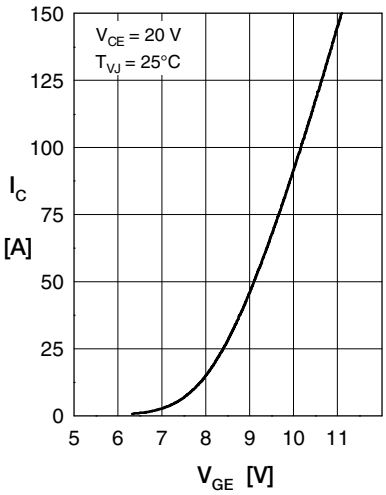


Fig. 3 Typ. transfer characteristics

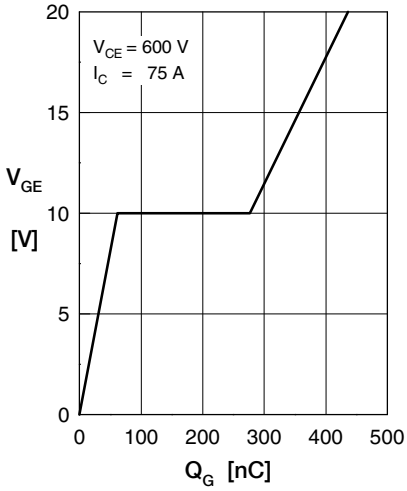


Fig. 4 Typ. turn-on gate charge

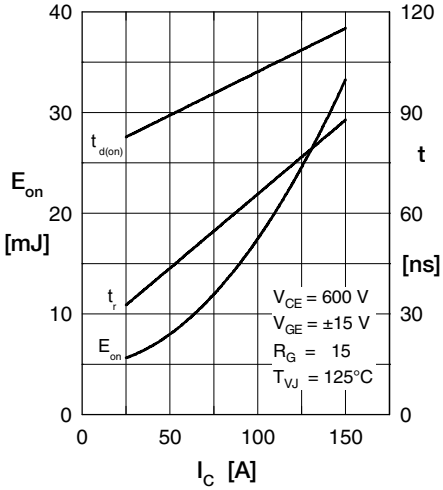


Fig. 5 Typ. turn on energy & switching times versus collector current

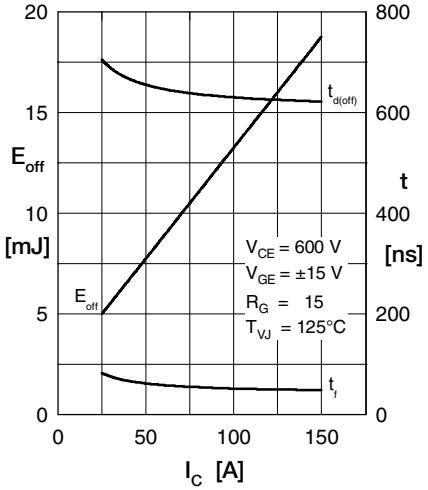


Fig.6 Typ. turn off energy & switching times versus collector current

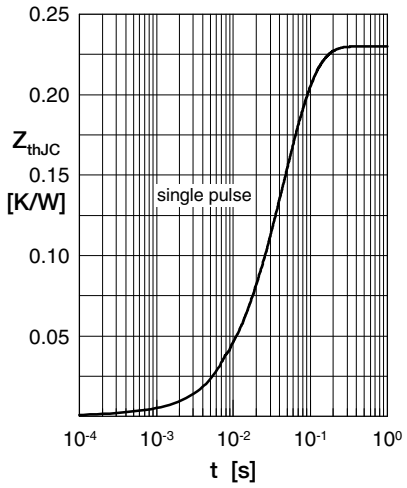


Fig. 12 Typical transient thermal impedance

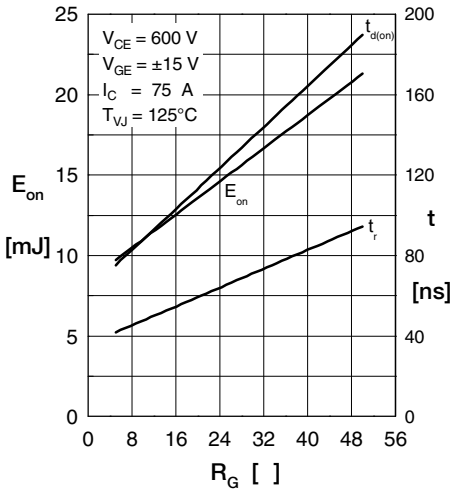


Fig. 9 Typ. turn on energy & switching times versus gate resistor

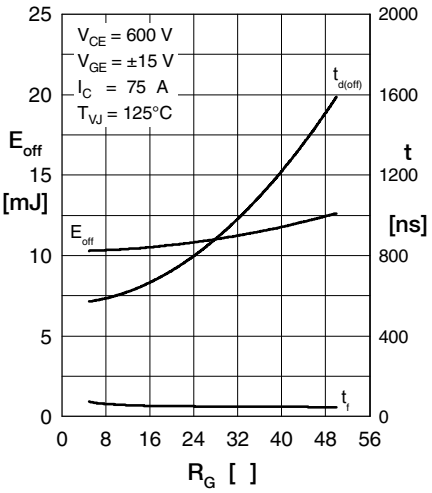


Fig. 9 Typ. turn off energy & switching times versus gate resistor

Diode

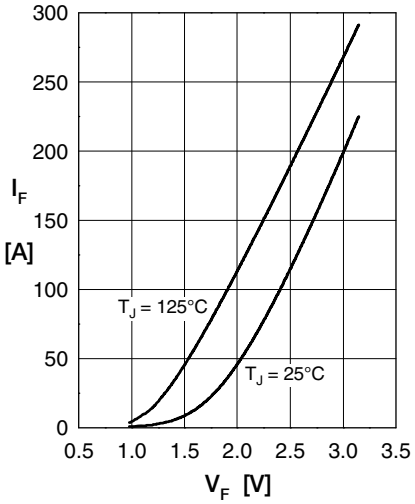


Fig. 1 Typ. Forward current vs. V_F

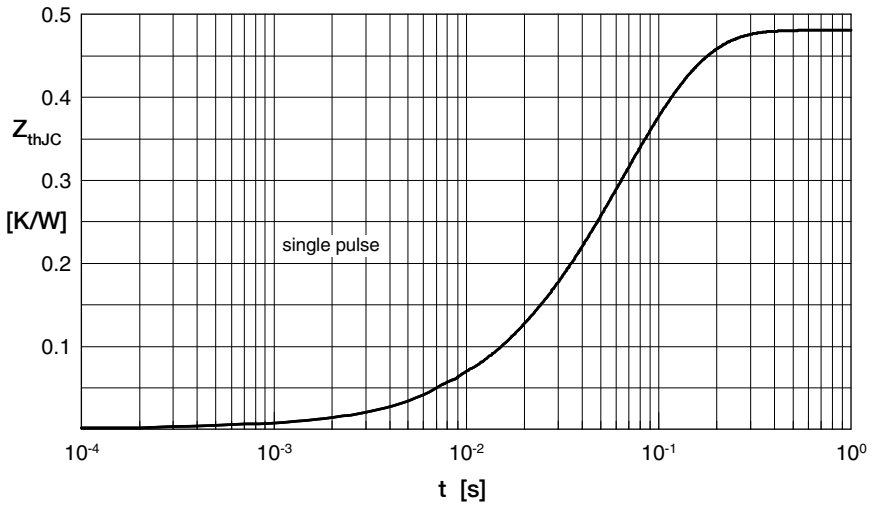


Fig. 2 Typ. transient thermal impedance junction to case